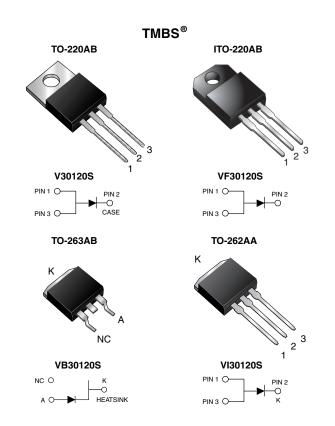


Vishay General Semiconductor

# **High-Voltage Trench MOS Barrier Schottky Rectifier**

Ultra Low  $V_F = 0.43 \text{ V}$  at  $I_F = 5 \text{ A}$ 

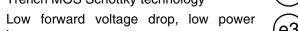


PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	30 A					
V <sub>RRM</sub>	120 V					
I <sub>FSM</sub>	300 A					
$V_F$ at $I_F = 30 A$	0.74 V					
T <sub>J</sub> max.	150 °C					

### **FEATURES**

losses





**e**3

High efficiency operation

Meets MSL level 1, per J-STD-020, LF COMPLIANT maximum peak of 245 °C (for TO-263AB package)

 Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

### **TYPICAL APPLICATIONS**

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

### **MECHANICAL DATA**

**Case:** TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	V30120S	VF30120S	VB30120S	VI30120S	UNIT	
Maximum repetitive peak reverse voltage	$V_{RRM}$	120			V		
Maximum average forward rectified current (fig. 1)	I <sub>F(AV)</sub>	30				Α	
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	300			А		
Non-repetitive avalanche energy at $T_J = 25$ °C, $L = 100$ mH	E <sub>AS</sub>	180				mJ	
Peak repetitive reverse current at $t_p = 2 \mu s$ , 1 kHz, $T_J = 38  ^{\circ}C \pm 2  ^{\circ}C$	I <sub>RRM</sub>	0.5			Α		
Voltage rate of change (rated V <sub>R</sub> )	dV/dt	10 000			V/µs		
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min	V <sub>AC</sub>	1500			V		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>STG</sub>	- 40 to + 150				°C	

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Breakdown voltage	I <sub>R</sub> = 1.0 mA	T <sub>A</sub> = 25 °C	$V_{BR}$	120 (minimum)	-	V	
Instantaneous forward voltage (1)	I <sub>F</sub> = 5 A I <sub>F</sub> = 15 A I <sub>F</sub> = 30 A	T <sub>A</sub> = 25 °C	V <sub>F</sub>	0.50 0.70 0.99	- - 1.10	V	
	I <sub>F</sub> = 5 A I <sub>F</sub> = 15 A I <sub>F</sub> = 30 A	T <sub>A</sub> = 125 °C		0.43 0.60 0.74	- - 0.82		
Reverse current (2)	V <sub>R</sub> = 90 V	T <sub>A</sub> = 25 °C T <sub>A</sub> = 125 °C		18 12	-	μA mA	
	V <sub>R</sub> = 120 V	T <sub>A</sub> = 25 °C T <sub>A</sub> = 125 °C	I <sub>R</sub>	- 22	500 35	μA mA	

#### Notes

 $^{(1)}$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

 $<sup>^{(2)}</sup>$  Pulse test: Pulse width  $\leq$  40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	V30120S	VF30120S	VB30120S	VI30120S	UNIT
Typical thermal resistance per diode	$R_{ hetaJC}$	1.6	4	1.6	1.6	°C/W

ORDERING INFORMATION (Example)								
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE			
TO-220AB	V30120S-E3/4W	1.88	4W	50/tube	Tube			
ITO-220AB	VF30120S-E3/4W	1.76	4W	50/tube	Tube			
TO-263AB	VB30120S-E3/4W	1.39	4W	50/tube	Tube			
TO-263AB	VB30120S-E3/8W	1.39	8W	800/reel	Tape and reel			
TO-262AA	VI30120S-E3/4W	1.46	4W	50/tube	Tube			

## **RATINGS AND CHARACTERISTICS CURVES**

 $(T_A = 25 \, ^{\circ}C \text{ unless otherwise noted})$ 

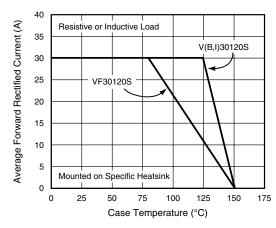


Figure 1. Forward Current Derating Curve

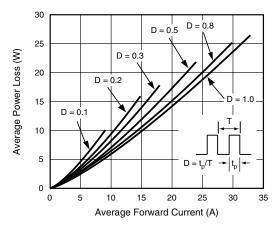


Figure 2. Forward Power Loss Characteristics Per Diode



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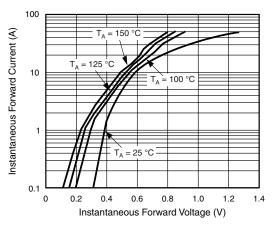


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

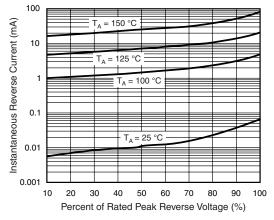


Figure 4. Typical Reverse Characteristics Per Diode

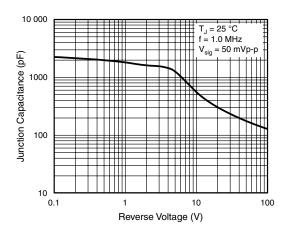


Figure 5. Typical Junction Capacitance Per Diode

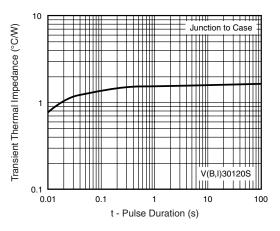


Figure 6. Typical Transient Thermal Impedance Per Diode

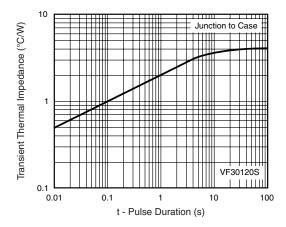
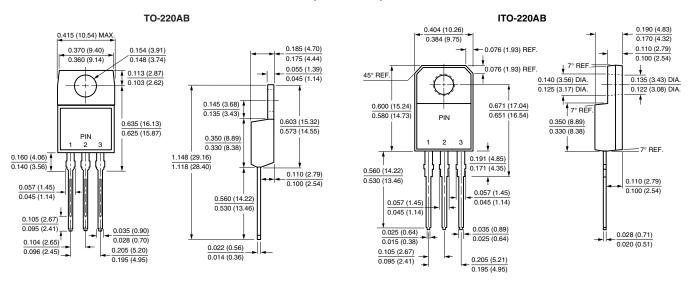


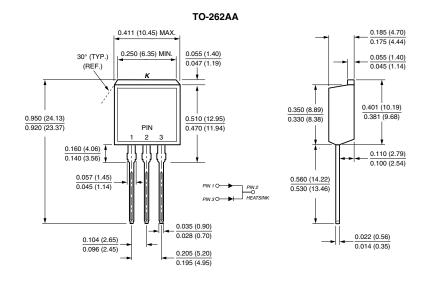
Figure 7. Typical Transient Thermal Impedance Per Diode

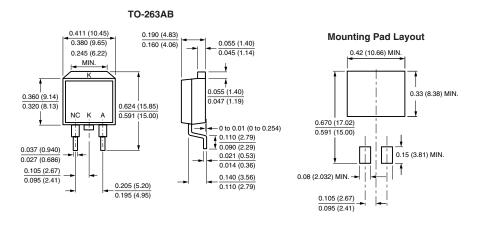
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### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)









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